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Technical Specifications for Single Avalanche Photo Diode (SPAD)

RFX NO. 610000817 (Reference No. 1000019958)

Single Avalanche Photo Diode (SPAD)

Photon Detection Efficiency(PDE)- The SPAD array should have a PDE of more than 12 % at 650 nm.

The APD should have a PDE of more than 3 % at 785 nm.

- Adjustable dead time- It should be between 50-125 ns.
- Frame rate- It should be at least 95 Kframes/sec with 8 bit.
- Dark count- less than 110 counts/sec. For at least 85% of the pixels.
- Active area diameter of each SPAD- 30 μ m.
- After pulsing probability should be less than or equal to 1 %.
- Interframe dead-time should be not more than 40 ns.

C-Mount capability.

Power Supply should be included.

Warranty for atleast 3 years.

software included

Time-Gated FLIM mode:

Gate Width: 5ns - 20ns

Gate Steps: 10- 20ps

Measurement Time range: 10-20ns.

Laser Sync Out: equal or above 50MHz